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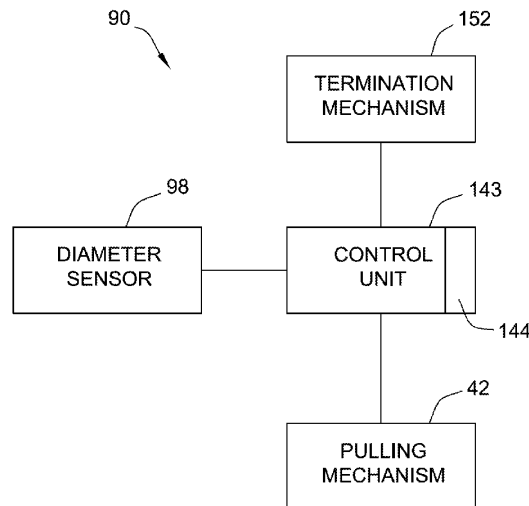


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(54) **Title:** METHODS FOR PRODUCING A SILICON INGOT THAT INVOLVE MONITORING A MOVING AVERAGE OF THE INGOT NECK PULL RATE

FIG. 4



(57) **Abstract:** Methods for producing monocrystalline silicon ingots in which the pull rate during neck growth is monitored are disclosed. A moving average of the pull rate may be calculated and compared to a target moving average to determine if dislocations were not eliminated and the neck is not suitable for producing an ingot main body suspended from the neck.

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